IN THE CLAIMS:

Please cancel claims 20-22.

Please amend claims 1, 8, and 13 in "clean" format, as follows:

1. (Amended twice) An organic electroluminescence device comprising:

an organic electroluminescence element and a thin film transistor which are formed on a substrate; said organic electroluminescence element having at least an organic emissive layer disposed between an anode and a cathode; said thin film transistor controlling a current flowing to said organic electroluminescence element; said thin film transistor having an active layer made of a semiconductor material;

a refractory metal layer connecting a source region or drain region of said thin film transistor to said anode of said organic electroluminescence element, said refractory metal layer, one of said source region and drain region, and said anode being laminated in a thickness direction of said substrate; and

a planarization insulating film covers said refractory metal layer,

wherein said anode is formed on said planarization insulating film, a contact hole is formed through the planarization insulating film, and said anode partially extends to said contact hole and said anode is in contact with said refractory metal layer.

8. (Amended twice) An organic electroluminescence device comprising:

pixels, each of said pixels including an organic electroluminescence element and a thin film transistor, said organic electroluminescence element having an emissive layer disposed between an anode and a cathode, said thin film transistor controlling a current flowing from a power source line to said organic electroluminescence element, said thin film transistor having an active layer made of a semiconductor material;

a contact between one of a source and drain in said active layer and said anode of said organic electroluminescence element, and between the other of said source and drain in said active layer and said power source line, said contact being achieved through a refractory metal layer, said refractory metal layer, one of said source and drain, and said anode being laminated in a thickness direction of said organic electroluminescence device; and

a planarization insulating film covers said refractory metal layer,

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wherein said anode is formed on said planarization insulating film, a contact hole is formed through the planarization insulating film, and said anode partially extends to said contact hole and said anode is in contact with said refractory metal layer.

13. (Amended twice) A light emitting device comprising:

an emissive element having an emissive layer between a first electrode and a second electrode;

a thin film transistor for controlling power supplied to said emissive element, said thin film transistor having an active layer made of a semiconductor material;

B3 a refractory metal layer connecting a first electrode region in said active layer to said first electrode of said emissive element, said refractory metal layer, said first electrode region and said first electrode being laminated in a thickness direction of said light emitting device;

a planarization insulating film covers said refractory metal layer;

an anode is formed on said planarization insulating film; and

a contact hole is formed through the planarization insulating film,

wherein said anode partially extends to said contact hole and said anode is in contact with said refractory metal layer.

Please add claim 23-26, as follows:

23. (Newly Added) The device defined in Claim 1, wherein said refractory metal layer of said source region is substantially identical in shape to said refractory metal layer of said drain region.

B4 24. (Newly Added) The device defined in Claim 4, wherein said conductive metal layer of said source region is substantially identical in shape to said conductive metal layer of said drain region.

25. (Newly Added) The device defined in Claim 8, wherein said refractory metal layer of said source region is substantially identical in shape to said refractory metal layer of said drain region.

26. (Newly Added) The device defined in Claim 10, wherein said conductive metal layer of said source region is substantially identical in shape to said conductive metal layer of said drain region.